

NOTICE TO Intelligent Epitaxy Technology CUSTOMERS**RoHS and Material Declaration Certificate****RoHS COMPLIANCE:**

- Epitaxial wafers supplied by Intelligent Epitaxy Technology comply with the EU RoHS Directive 2011/65/EU and amendment (EU) 2015/863.
- Materials that are used in the production of epitaxial wafers supplied by Intelligent Epitaxy Technology are ultra-high purity and contain well below the maximum concentration values of EU RoHS substances, as listed below.

EU RoHS substances in materials and their maximum concentration values (MCVs)

1. Lead (Pb) < 0.10% = < 1,000 PPM
2. Mercury (Hg) < 0.10% = < 1,000PPM
3. Hexavalent Chromium (Cr VI) < 0.10% = < 1,000PPM
4. Cadmium (Cd) < 0.01% = < 100 PPM
5. Polybrominated Biphenyls (PBB) < 0.10% = < 1,000PPM
6. Polybrominated Diphenyl Ethers (PBDE) < 0.10% = < 1,000PPM
7. Bis(2-Ethylhexyl) phthalate (DEHP) < 0.10% = < 1000 PPM
8. Benzyl butyl phthalate (BBP) < 0.10% = < 1000 PPM
9. Dibutyl phthalate (DBP) < 0.10% = < 1000 PPM
10. Diisobutyl phthalate (DIBP) < 0.10% = < 1000 PPM

SUBSTANCES OF CONCERN:

- Epitaxial wafers supplied by Intelligent Epitaxy Technology do not contain chlorinated organic compounds (e.g. PBBs or PBDEs), organic tin compounds, asbestos, AZO compounds, formaldehyde, ozone depleters, residual monomers, benzene or poly vinyl chloride.

SUBSTANCES USED IN PRODUCTION OF INTELLIEPI EPITAXIAL WAFERS:

Component	Substance	CAS#
Substrate	Gallium Arsenide (GaAs)	1303-00-0
Substrate	Indium Phosphide (InP)	22398-80-7
Epitaxy Source Material	Gallium (Ga)	7440-55-3
Epitaxy Source Material	Aluminum (Al)	7429-90-5
Epitaxy Source Material	Indium (In)	7440-746
Epitaxy Source Material	Arsenic (As)	7440-38-2
Epitaxy Source Material	Phosphorus (P)	7723-14-0
Epitaxy Source Material	Antimony (Sb)	7440-36-0
Dopant	Silicon (Si)	7440-21-3
Dopant	Iron (Fe)	7439-89-6
Dopant	Sulfur (S)	7704-34-9
Dopant	Carbon (C)	7440-44-0
Dopant	Beryllium (Be)	7440-41-7

Intelligent Epitaxy Technology, Inc.



Jerry Sinnie, Quality Manager
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